IN THE CLAIMS:

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1. (Currently Amended) A method for driving a solid-state image pickup device which stores, in a plurality of photo-electric conversion units, signal charges corresponding to an incident light during a prescribed time period, each of said photo-electric conversion units being provided with an overflow drain (OFD) structure, excludes surplus charges from said photo-electric conversion units by an electric potential barrier, said electric potential barrier being maintained between said OFD structure and each of said photo-electric conversion units, reads out, after cutting off said incident light by a cut-off means such as a mechanical shutter, said signal charges by grouping said photo-electric conversion units into a prescribed number of regions, and outputs image signal from all of the photo-electric conversion units by repeating the read-out procedures, which comprises the steps of:

cutting off said incident light;
raising up said electric potential barrier; and
starting reading out said signal charges.

2. (Previously Presented) The method for driving a solid-state image pickup device according to Claim 1, wherein said electric potential barrier during the read-out step is raised up by a voltage greater than 0.4.V.

3.-4. (Canceled).

5. (Currently Amended) The method for driving a solid-state image pickup device according to Claim 1, wherein said OFD structure is a vertical OFD structure which excludes the surplus charges from said photo-electric conversion units by said electric potential barrier by a voltage applied to a substrate of said vertical OFD structure, which comprises the steps of:

cutting off said incident light;

raising up said electric potential barrier; <u>and</u> starting reading out said signal charges.

6. (Previously Presented) The method for driving a solid-state image pickup device according to Claim 5, wherein said electric potential barrier during the read-out step is raised up by a voltage greater than 0.4V.

7.-8. (Canceled).

9. (Currently Amended) The method for driving a solid-state image pickup device according to Claim 1, wherein said OFD structure is a horizontal OFD structure which excludes the surplus charges from said photo-electric conversion units by said electric potential barrier by a voltage applied to a gate of said horizontal OFD structure, which comprises the steps of:

cutting off said incident light;
raising up said electric potential barrier; and
starting reading out said signal charges.

10. (Previously Presented) The method for driving a solid-state image pickup device according to Claim 9, wherein said electric potential barrier during the read-out step is raised up by a voltage greater than 0.4V.

11.-12. (Canceled).

- 13. (New) The method for driving a solid-state image pickup device according to Claim 1, wherein said signal charges are read out from said photo-electric conversion units through signal read-out portions and the electric potential of said electric potential barrier during the read-out step is deeper than an electric potential which is applied in signal read-out portion during the times except said read-out step.
- 14. (New) The method for driving a solid-state image pickup device according to Claim 13, wherein the potential different between said electric potential of said electric potential barrier during the read-out step and said electric potential which is applied in said signal read-out portion is greater than 0.4V.
- 15. (New) The method for driving a solid-state image pickup device according to Claim 5, wherein said signal charges are read out from said photo-electric conversion units through signal read-out portions and the electric potential of said electric potential barrier during the read-out step is deeper than an electric potential which is applied in signal read-out portion during the times except said read-out step.

- 16. (New) The method for driving a solid-state image pickup device according to Claim 15, wherein the potential difference between said electric potential of said electric potential barrier during the read-out step and said electric potential which is applied in said signal read-out portion is greater than 0.4V.
- 17. (New) The method for driving a solid-state image pickup device according to Claim 9, wherein said signal charges are read out from said photo-electric conversion units through signal read-out portions and the electric potential of said electric potential barrier during the read-out step is deeper than an electric potential which is applied in signal read-out portion during the times except said read-out step.
- 18. (New) The method for driving a solid-state image pickup device according to Claim 17, wherein the potential difference between said electric potential of said electric potential barrier during the read-out step and said electric potential which is applied in said signal read-out portion is greater than 0.4V.